PSZ10065C

650V 10A 350mΩ Si Super junction MOSFET with Zener diode

PowerCubeSemi, Inc.
Potential · Convergence · Smart

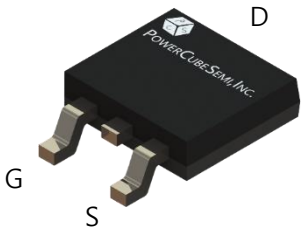
Features

Si Super junction MOSFET

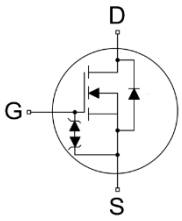
- Rated to 650V at 10Amps @T_C= 25℃
- Max $R_{DS(on)}$ = 350 mΩ
- Gate Charge(Typ. Q_g=20 nC)
- Improved dv/dt Capability
- 100% Avalanche Tested
- Excellent ESD robustness

Application

- LCD/LED/PDP TV
- Telecom/Server Power supplies
- AC-DC Power Supply
- LED Lighting



PKG type : DPAK (TO-252)



Halogen-Free

RoHS

Description

PSZ10065C is PowerCubeSemi's second generation of high voltage Super Junction MOSFET that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate and higher avalanche energy. Consequently, the combination of Super Junction MOSFET is suitable for various AC/DC power conversion for system miniaturization and higher efficiency

Absolute Maximum Ratings

Symbol	Parameter	Test Condition	Value	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=1㎃	650	V
I_D	Drain Current	T_c=25℃	10	A
I_{DM}	Pulsed Drain Current	Pulse width limited by junction temperature	30	A
V_{GS}	Gate-Source Voltage		±30	V
E_{AS}	Single Pulsed Avalanche Energy	V_{DD}=50V, I_D=4A, L=20mH	160	mJ
P_d	Power Dissipation		36.7	W
T_J	Operating Junction Temperature		150	℃
T_{stg}	Storage Temperature		-55 to 150	℃

Package Marking and Ordering Information

Device Marking	Device	Package	Packing Method	Quantity
PSZ10065C	PSZ10065	TO-252	TUBE & REEL	-

Electrical Characteristics of Si MOSFET

Symbol	Parameter	Test Condition	Numerical			Unit
			Min	Typ.	Max.	
BV_{DSS}	Drain-source breakdown voltage	V_{GS} = 0V, I_D=1㎃, T_C=25°C	650	-	-	V
I_{DSS}	Zero gate voltage drain current	V_{DS}=650V, V_{GS}=0V	-	-	10	μA
I_{GSS}	Gate-source leakage current	V_{GS}=±30V, V_{DS}=0V	-	-	±5	μA
$V_{GS(th)}$	Gate threshold voltage	V_{DS}=V_{GS}, I_D=1㎃	3.5	-	4.5	V
$R_{DS(ON)}$	Static drain-source on state resistance	V_{GS}=10V, I_D=5A	-	330	350	mΩ
$t_{d(on)}$	Turn-on delay time	V_{DD}=380 V, I_D=5A, V_{GS}=10 V, R_G=4.7Ω	-	16	-	ns
T_r	Turn-on rise time		-	8	-	
$t_{d(off)}$	Turn-off delay time		-	48	-	
T_f	Turn-off fall time		-	12	-	

Electrical Characteristics of Si MOSFET

Symbol	Parameter	Test Condition	Numerical		Unit
			Typ.	Max.	
$R_{\theta JC}$	Thermal resistance, Junction to case		3.4	-	℃/W
R_g	Gate resistance	V_{GS} = 0V, f = 1㎒	8	-	Ω
C_{iss}	Input capacitance	V_{DS} = 380V, V_{GS} = 0V, f = 1㎒	840	-	pF
C_{oss}	Output capacitance		21	-	
C_{rss}	Reverse transfer capacitance		2	-	
$Q_{g(tot)}$	Total gate charge at 10V	V_{DS} = 380V, I_D = 10A $V_{GS(on)}$ = 10V	20	-	nC
Q_{gs}	Gate to source gate charge		3.5	-	
Q_{gd}	Gate to drain “Miller” charge		9	-	

Electrical Characteristics of Si Diode

Symbol	Parameter	Test Condition	Numerical		Unit
			Typ.	Max.	
I_S	Diode forward current		-	10	A
I_{SM}	Pulsed diode forward current		-	30	A
V_{SD}	Source to drain diode forward voltage	I_{SD} = 10A, V_{GS} = 0V	-	1.2	V
T_{rr}	Reverse recovery time	I_{SD} = 5A, V_{DD} = 400V, dI_F/dt=100A/㎲	230	-	ns
Q_{rr}	Reverse recovery charge		2.6	-	μC
I_{rrm}	Reverse recovery current		22	-	A

Typical Characteristics

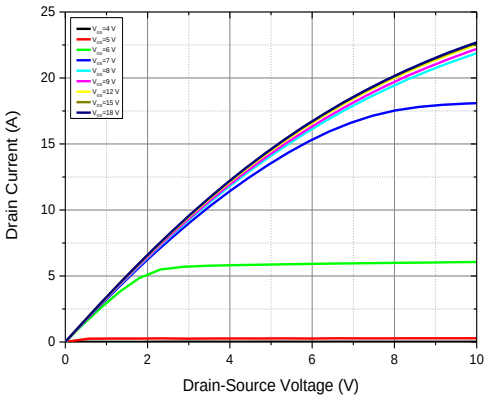


Figure 1. On-state characteristics

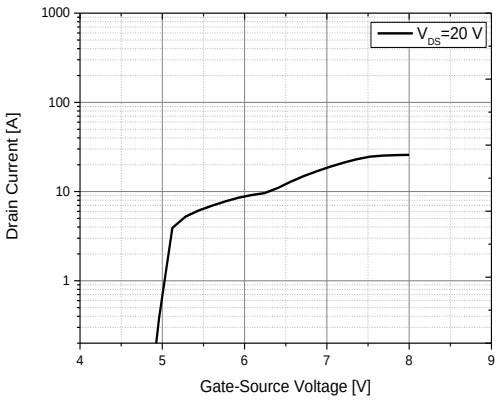


Figure 2. Transfer Characteristics

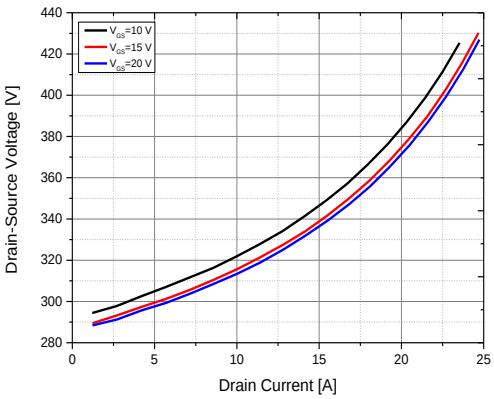


Figure 3. On Resistance Variation vs Drain Current and Gate Voltage

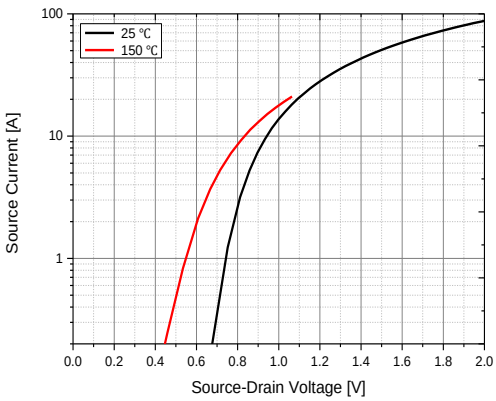


Figure 4. Body Forward Voltage Variation vs Source Current and Temperature

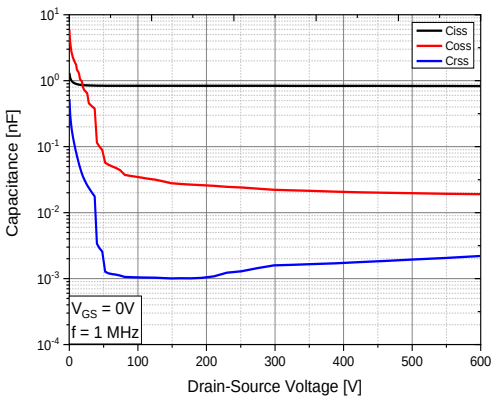


Figure 5. Capacitance Characteristics

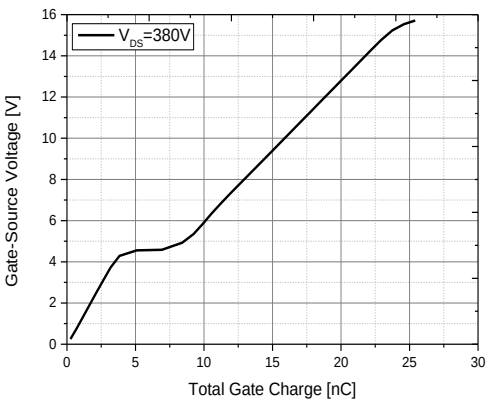


Figure 6. Gate Charge Characteristics

Typical Characteristics

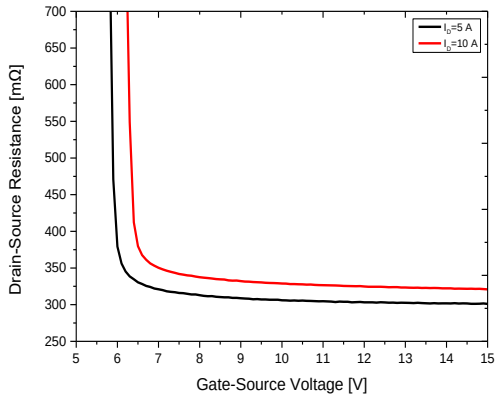


Figure 7. Drain to Source Resistance vs Gate to Source Voltage

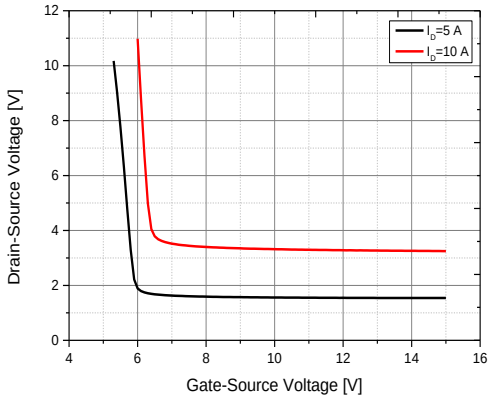


Figure 8. Drain to Source Voltage vs Gate to Source Voltage

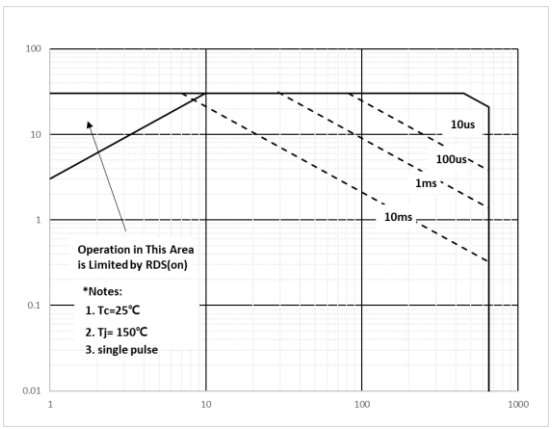


Figure 9. Safe Operating Area

Package Outline

[Unit : mm]